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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/810,633	03/29/2004	Kazuyuki Mitsuoka	251232US2	9585
22850 7590 05/15/2007 OBLON, SPIVAK, MCCLELLAND, MAIER & NEUSTADT, P.C.			EXAMINER	
1940 DUKE ST	REET	YOUNG, CHRISTOPHER G		
ALEXANDRIA, VA 22314			ART UNIT	PAPER NUMBER
			1756	
			NOTIFICATION DATE	DELIVERY MODE
			05/15/2007	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

patentdocket@oblon.com oblonpat@oblon.com jgardner@oblon.com

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	Application No.	Applicant(s)				
	10/810,633	MITSUOKA ET AL.				
Office Action Summary	Examiner	Art Unit				
	Christopher G. Young	1756				
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with th	ne correspondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period v. - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICAT 36(a). In no event, however, may a reply by will apply and will expire SIX (6) MONTHS (6), cause the application to become ABANDO	ION. se timely filed from the mailing date of this communication. DNED (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on 3-29		<u>005</u> .				
,	·—					
3) Since this application is in condition for allowal						
closed in accordance with the practice under E	:x рапе Quayle, 1935 С.D. 11	, 453 O.G. 213.				
Disposition of Claims						
4) Claim(s) 1-13 is/are pending in the application						
4a) Of the above claim(s) is/are withdraw	wn from consideration.					
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>1-13</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/o	r election requirement.					
Application Papers						
9) The specification is objected to by the Examine	er.					
10)⊠ The drawing(s) filed on 29 March 2004 is/are:	a)⊠ accepted or b)⊡ objecte	ed to by the Examiner.				
Applicant may not request that any objection to the	drawing(s) be held in abeyance.	See 37 CFR 1.85(a).				
Replacement drawing sheet(s) including the correct						
11) ☐ The oath or declaration is objected to by the Ex	kaminer. Note the attached Of	fice Action or form PTO-152.				
Priority under 35 U.S.C. § 119						
12)⊠ Acknowledgment is made of a claim for foreign a)⊠ All b)□ Some * c)□ None of:	priority under 35 U.S.C. § 11	9(a)-(d) or (f).				
1.⊠ Certified copies of the priority document	s have been received.					
2. Certified copies of the priority document	s have been received in Appli	cation No				
3. Copies of the certified copies of the prio	rity documents have been rec	eived in this National Stage				
application from the International Burea	u (PCT Rule 17.2(a)).					
* See the attached detailed Office action for a list	of the certified copies not reco	eived.				
Attachment(s)	. □	(DTO 412)				
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) 		nary (PTO-413) ail Date				
3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date 1 sheet.	5) Notice of Inform 6) Other:	nal Patent Application				

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DETAILED ACTION

Priority

1. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Information Disclosure Statement

2. The information disclosure statement (IDS) submitted on December 23, 2005 has been considered by the examiner.

Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 4. Claims 1-13 are rejected under 35 U.S.C. 102(e) as being anticipated by Livesay et al., US Patent Number 6,607,991.

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The instant application is drawn to an electron beam processing method and apparatus for its practice. The prior art reference to Livesay et al. describes, teaches and suggests all of the claimed embodiments of the instant application. An electron beam exposure method is described which provides a means of curing spin-on-glass or spin-on-polymer dielectric material formed on a semiconductor wafer. The dielectric material insulates the conductive metal layer and planarizes the topography in the process of manufacturing multilayered integrated circuits. The method utilizes a large area, uniform electron beam exposure system in a soft vacuum environment. A wafer coated with uncured dielectric material is irradiated with electrons of sufficient energy to penetrate the entire thickness of the dielectric material and is simultaneously heated by infrared heaters. By adjusting the process conditions, such as electron beam total dose and energy, temperature of the wafer, and ambient atmosphere, the properties of the cured dielectric material can be modified.

Column 7 discloses in part that during the electron beam curing process, the wafer is kept at a temperature between 10.degree. and 1000.degree. C. Preferably, the wafer temperature is between 30 and 500.degree. C. and most preferably between 200.degree. and 400.degree. C. The infrared quartz lamps 36 are on continuously until the wafer temperature reaches the desired process temperature. The lamps are turned off and on at varying duty cycle to control the wafer temperature. Typical background process gases in the soft vacuum environment include nitrogen, argon, oxygen, ammonia, forming gas, helium, methane, hydrogen, silane, and mixtures thereof. For many dielectric materials, a non-oxidizing processing atmosphere is used. For other applications, such as complete conversion of siloxane material to silicon dioxide, an oxidizing atmosphere would be appropriate. The optimal choice of electron beam dose, energy,

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and current, processing temperature, and process gas depends on the composition of the spin-onglass or spin-on-polymer material.

Furthermore, claim 16 of the patent teaches the particular partial pressures utilized during the exposure process. The particular materials of the coating are taught throughout the entire document, and the Examiner asserts that the same or similar compounds and compositions are being utilized, and one of skill would expect that they would exhibit the same or similar property characteristics as those claimed.

Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Christopher G. Young whose telephone number is 571-272-1394. The examiner can normally be reached on Monday-Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Mark Huff can be reached on 571-272-1385. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Christopher G. Young Primary Examiner Art Unit 1756